MITSUBISHI Nch POWER MOSFET

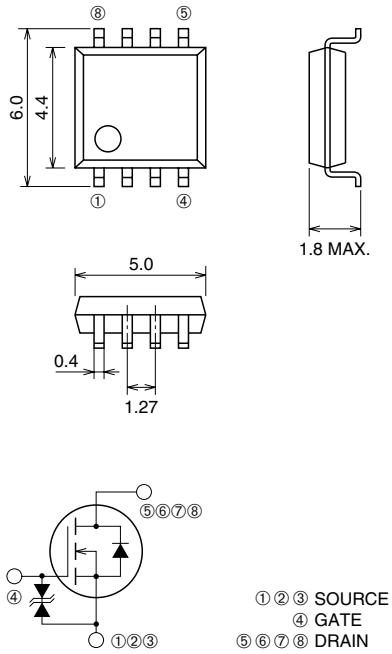
FY14AAJ-03F

HIGH-SPEED SWITCHING USE

FY14AAJ-03F

- 4V DRIVE
- V_{DSS} 30V
- $r_{DS\ (ON)}$ (MAX) 8.1mΩ
- I_D 14A

OUTLINE DRAWING Dimensions in mm



SOP-8

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	V_{GS} = 0V	30	V
V_{GSS}	Gate-source voltage	V_{DS} = 0V	±20	V
I_D	Drain current		14	A
I_{DM}	Drain current (Pulsed)		98	A
I_{DA}	Avalanche drain current (Pulsed)	L = 10μH	14	A
I_S	Source current		2.1	A
I_{SM}	Source current (Pulsed)		8.2	A
P_D	Maximum power dissipation		2.3	W
T_{ch}	Channel temperature		–55~+150	°C
T_{stg}	Storage temperature		–55~+150	°C
—	Weight	Typical value	0.07	g

MITSUBISHI ELECTRIC

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS} = 0V	30	—	—	V
$V_{(BR)GSS}$	Gate-source breakdown voltage	I_G = ±100μA, V_{GS} = 0V	±20	—	—	V
I_{DSS}	Drain-source leakage current	V_{DS} = 30V, V_{GS} = 0V	—	—	0.1	mA
I_{GSS}	Gate-source leakage current	V_{GS} = ±20V, V_{DS} = 0V	—	—	±10	μA
$V_{GS\ (th)}$	Gate-source threshold voltage	I_D = 1mA, V_{DS} = 10V	1.0	1.5	2.0	V
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 14A, V_{GS} = 10V	—	6.5	8.1	mΩ
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 7A, V_{GS} = 4.5V	—	8.8	12.0	mΩ
$r_{DS\ (ON)}$	Drain-source on-state resistance	I_D = 7A, V_{GS} = 4V	—	10.0	14.0	mΩ
$V_{DS\ (ON)}$	Drain-source on-state voltage	I_D = 14A, V_{GS} = 10V	—	0.091	0.113	V
$\lvert y_{fs} \rvert$	Forward transfer admittance	I_D = 14A, V_{DS} = 10V	—	30	—	S
C_{iss}	Input capacitance	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz	—	2600	—	pF
C_{oss}	Output capacitance		—	750	—	pF
C_{rss}	Reverse transfer capacitance		—	350	—	pF
$t_{d\ (on)}$	Turn-on delay time	V_{DD} = 15V, I_D = 7A, V_{GS} = 5V, R_G = 5Ω	—	22	—	ns
t_r	Rise time		—	22	—	ns
$t_{d\ (off)}$	Turn-off delay time		—	60	—	ns
t_f	Fall time		—	22	—	ns
Q_g	Total gate charge	V_{DD} = 15V, V_{GS} = 10V, I_D = 14A	—	53	—	nC
Q_{gs}	Gate-source charge		—	6	—	nC
Q_{gd}	Gate-drain charge		—	15	—	nC
V_{SD}	Source-drain voltage	I_S = 2.1A, V_{GS} = 0V	—	0.75	1.10	V
$R_{th\ (ch-a)}$	Thermal resistance	Channel to air	—	—	54.3	°C/W
t_{rr}	Reverse recovery time	I_S = 2.1A, di_S/dt = –50A/μs	—	40	—	ns